

<b>L Number</b>	<b>Hits</b>	<b>Search Text</b>	<b>DB</b>	<b>Time stamp</b>
<b>1</b>	<b>44</b>	<b>((tft or (thin near film near transistor)) with (insulating or dielectric) with gate with electrode with (semiconductor adj layer) with (source or drain or source/drain) with (passivation or passivating or protective) with (porous or amorphous or pore or porosity)</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/09/14 11:38</b>
<b>2</b>	<b>8</b>	<b>((tft or (thin near film near transistor)) with (insulating or dielectric) with gate with electrode with (semiconductor adj layer) with (source or drain or source/drain) with (passivation or passivating or protective) with (porous or amorphous or pore or porosity)).ti,ab,clm.</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/09/14 11:41</b>
<b>3</b>	<b>2</b>	<b>((tft or (thin near film near transistor)) with (insulating or dielectric) with gate with electrode with (semiconductor adj layer) with (source or drain or source/drain) with (passivation or passivating or protective) with (porous or amorphous or pore or porosity) with (charge or ion or implantation or impurity)).ti,ab,clm.</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/09/14 11:41</b>
<b>4</b>	<b>1</b>	<b>((tft or (thin near film near transistor)) with (insulating or dielectric) with gate with electrode with (semiconductor adj layer) with (source or drain or source/drain) with (passivation or passivating or protective) with (porous or amorphous or pore or porosity)).ti,ab,clm. and ((amorphous or pore or porous or porosity) near5 (semiconductor adj layer) near5 (charge or impurity or ion or doping))</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/09/14 11:43</b>
<b>5</b>	<b>8</b>	<b>((tft or (thin near film near transistor)) with (insulating or dielectric) with gate with electrode with (semiconductor adj layer) with (source or drain or source/drain) with (passivation or passivating or protective) with (porous or amorphous or pore or porosity)).ti,ab,clm.</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/09/14 11:43</b>
<b>6</b>	<b>6</b>	<b>((tft or (thin near film near transistor)) with (insulating or dielectric) with gate with electrode with (semiconductor adj layer) with (source or drain or source/drain) with (passivation or passivating or protective) with (porous or amorphous or pore or porosity)) and ((amorphous or pore or porous or porosity) near5 (semiconductor adj layer) near5 (charge or impurity or ion or doping))</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2004/09/14 11:45</b>

7	6	((tft or (thin near film near transistor)) with (insulating or dielectric) with gate with electrode with (semiconductor adj layer) with (source or drain or source/drain) with (passivation or passivating or protective) with (porous or amorphous or pore or porosity)) and ((amorphous or pore or porous or porosity) near5 (semiconductor adj layer) near5 (passivation or protective))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:45
8	4	((tft or (thin near film near transistor)) with (insulating or dielectric) with gate with electrode with (semiconductor adj layer) with (source or drain or source/drain) with (passivation or passivating or protective) with (porous or amorphous or pore or porosity)) and ((amorphous or pore or porous or porosity) near3 (semiconductor adj layer) near3 (passivation or protective))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:47
10	1	((tft or (thin near film near transistor)) with (insulating or dielectric) with gate with electrode with (semiconductor adj layer) with (source or drain or source/drain) with (passivation or passivating or protective) with (porous or amorphous or pore or porosity)).clm. and ((amorphous or pore or porous or porosity) near5 (semiconductor adj layer) near5 (passivation or protective)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:48
9	2	((tft or (thin near film near transistor)) with (insulating or dielectric) with gate with electrode with (semiconductor adj layer) with (source or drain or source/drain) with (passivation or passivating or protective) with (porous or amorphous or pore or porosity)) and ((amorphous or pore or porous or porosity) near5 (semiconductor adj layer) near5 (passivation or protective)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:48
11	2	((tft or (thin near film near transistor)) with (insulating or dielectric) with gate with electrode with (semiconductor adj layer) with (source or drain or source/drain) with (passivation or passivating or protective) with (porous or amorphous or pore or porosity)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/14 11:49